

TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR ILLICON PLANAR TYPE

## SM25GZ51, SM25JZ51

### AC POWER CONTROL APPLICATIONS

- Repetitive Peak Off-State Voltage:  $V_{DRM} = 400V, 600V$
- R.M.S On-State Current:  $I_T (RMS) = 25A$
- High Commutating ( $dv / dt$ ): ( $dv / dt$ )  $c = 10V / \mu s$
- Isolation Voltage:  $V_{Isol} = 1500V AC$

### MAXIMUM RATINGS

CHARACTERISTIC		SYMBOL	RATING	UNIT
Repetitive Peak Off-State Voltage	SM25GZ51	$V_{\text{DRM}}$	400	V
	SM25JZ51		600	
R.M.S On-State Current (Full Sine Waveform $T_c = 73^{\circ}\text{C}$ )		$I_{\text{T (RMS)}}$	25	A
Peak One Cycle Surge On-State Current (Non-Repetitive)		$I_{\text{TSM}}$	230 (50Hz)	A
			253 (60Hz)	
$I^2t$ Limit Value		$I^2t$	260	$\text{A}^2\text{s}$
Critical Rate of Rise of On-State Current (Note 1)		$di / dt$	50	$\text{A} / \mu\text{s}$
Peak Gate Power Dissipation		$P_{\text{GM}}$	5	W
Average Gate Power Dissipation		$P_{\text{G (AV)}}$	0.5	W
Peak Gate Voltage		$V_{\text{GM}}$	10	V
Peak Gate Current		$I_{\text{GM}}$	2	A
Junction Temperature		$T_{\text{j}}$	-40~125	$^{\circ}\text{C}$
Storage Temperature Range		$T_{\text{stg}}$	-40~125	$^{\circ}\text{C}$
Isolation Voltage (AC, $t = 1 \text{ min.}$ )		$V_{\text{Isol}}$	1500	V

Note 1:  $di / dt$  Test Condition

$$V_{DRM} = 0.5 \times \text{Rated}$$

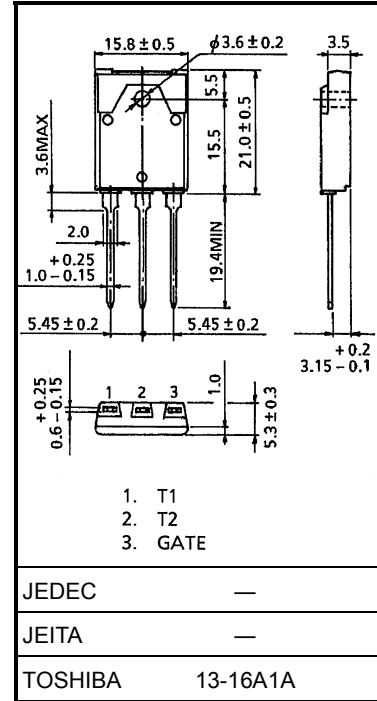
$$I_{TM} \leq 40A$$

$$t_{gw} \geq 10\mu s$$

$$t_{gr} \leq 250ns$$

$$i_{gp} = I_{GT} \times 2.0$$

Unit: mm

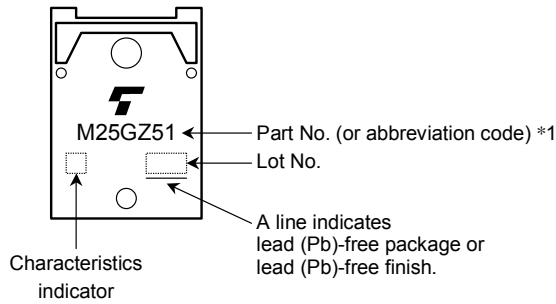


Weight: 5.9 g (typ.)

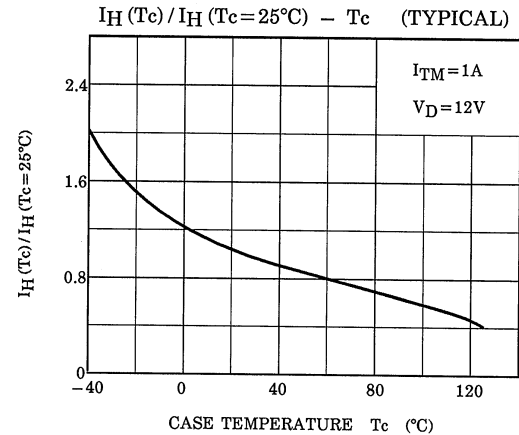
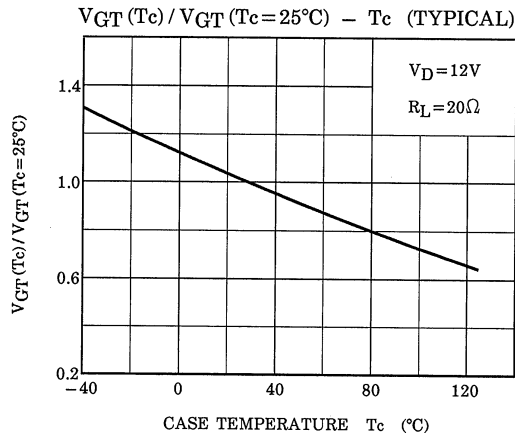
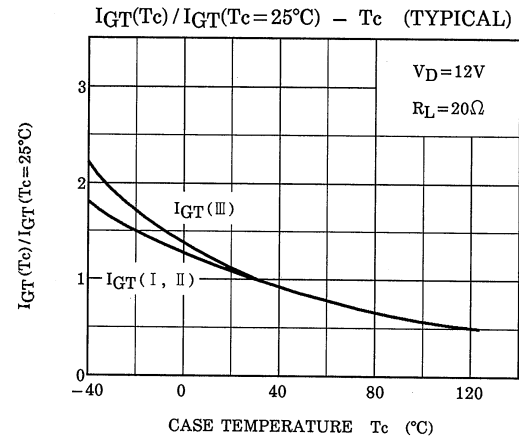
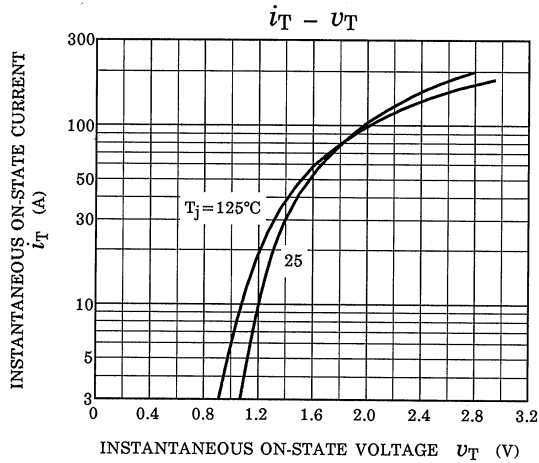
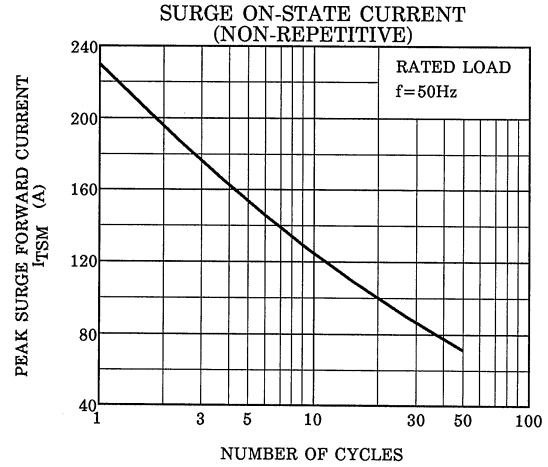
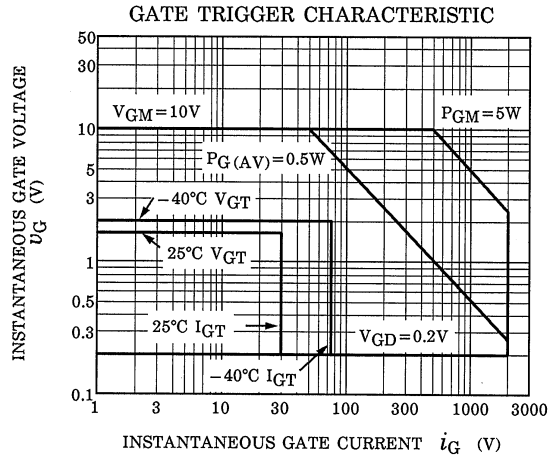
## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

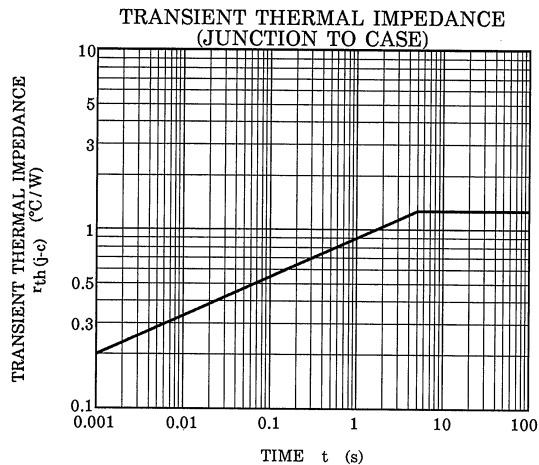
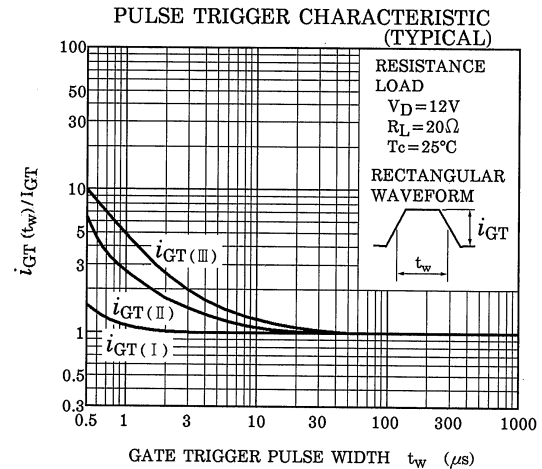
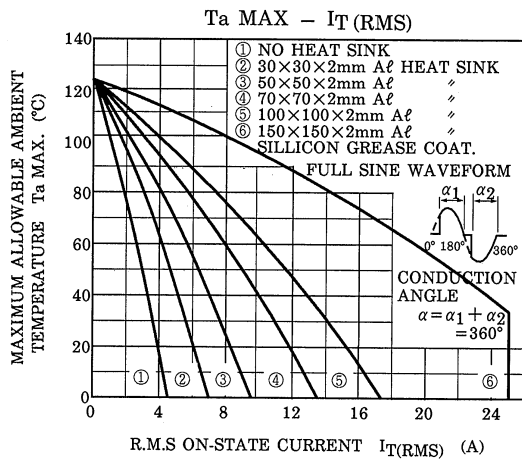
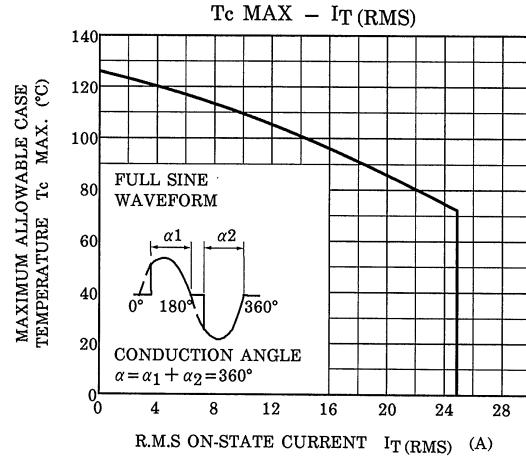
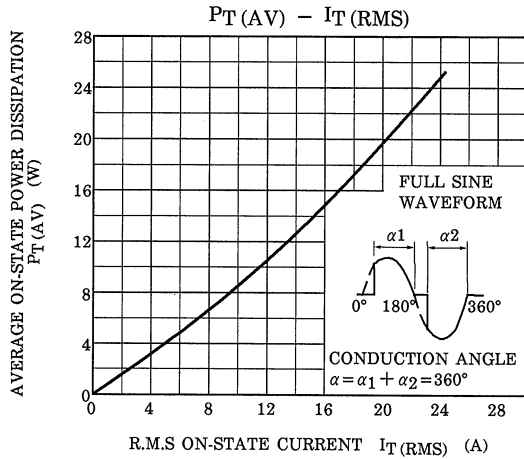
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT	
Repetitive Peak Off-State Current		I <sub>DRM</sub>	V <sub>DRM</sub> = Rated	—	—	20	μA	
Gate Trigger Voltage	I	V <sub>GT</sub>	V <sub>D</sub> = 12V R <sub>L</sub> = 20Ω	T2 (+) , Gate (+)	—	—	1.5	V
	II			T2 (+) , Gate (−)	—	—	1.5	
	III			T2 (−) , Gate (−)	—	—	1.5	
Gate Trigger Current	I	I <sub>GT</sub>	V <sub>D</sub> = 12V R <sub>L</sub> = 20Ω	T2 (+) , Gate (+)	—	—	30	mA
	II			T2 (+) , Gate (−)	—	—	30	
	III			T2 (−) , Gate (−)	—	—	30	
Peak On-State Voltage		V <sub>TM</sub>	I <sub>TM</sub> = 40A	—	—	1.5	V	
Gate Non-Trigger Voltage		V <sub>GD</sub>	V <sub>D</sub> = Rated, T <sub>c</sub> = 125°C	0.2	—	—	V	
Holding Current		I <sub>H</sub>	V <sub>D</sub> = 12V, I <sub>TM</sub> = 1A	—	—	60	mA	
Thermal Resistance		R <sub>th</sub> (j-c)	Junction to Case, AC	—	—	1.3	°C / W	
Critical Rate of Rise of Off-State Voltage		dv / dt	V <sub>DRM</sub> = Rated, T <sub>j</sub> = 125°C Exponential Rise	—	300	—	V / μs	
Critical Rate of Rise of Off-State Voltage at Commutation		(dv / dt) c	V <sub>DRM</sub> = 400V, T <sub>j</sub> = 125°C (di / dt) c = − 15A / ms	10	—	—	V / μs	

## MARKING



*1	Part No. (or abbreviation code)	Part No.
	M25GZ51	SM25GZ51
	M25JZ51	SM25JZ51





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